

FDD6672A

30V N-Channel PowerTrench^O MOSFET

General Description

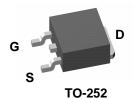
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $R_{\rm DS(ON)}$ and fast switching speed.

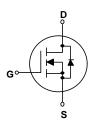
Applications

• DC/DC converter

Features

- 65 A, 30 V. $R_{DS(ON)} = 9.5 \text{ m}\Omega$ @ $V_{GS} = 4.5 \text{ V}$ $R_{DS(ON)} = 8 \text{ m}\Omega$ @ $V_{GS} = 10 \text{ V}$
- High performance trench technology for extremely low $R_{\mbox{\scriptsize DS(ON)}}$
- Low gate charge (33 nC typical)
- · High power and current handling capability





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V _{DSS}	Drain-Source Voltage		30	V
V_{GSS}	Gate-Source Voltage		±12	V
I _D	Drain Current - Continuous	(Note 1a)	65	А
	– Pulsed		100	
P _D	Maximum Power Dissipation @ T _C = 25°C	(Note 1)	70	W
	@ T _A = 25°C	(Note 1a)	3.2	
	@ T _A = 25°C	(Note 1b)	1.3	
T _J , T _{STG}	Operating and Storage Junction Temperatu	-55 to +150	°C	

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	1.8	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1b)	96	°C/W

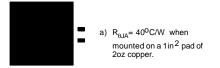
Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDD6672A	FDD6672A	13"	16mm	2500 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	racteristics					l
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	30			V
ΔBV _{DSS} ΔT _J	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu A$, Referenced to 25°C		20		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ
I _{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = 12 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -12 \text{ V } V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)		•			•
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.8	1.2	2.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C		-4		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$V_{GS} = 4.5 \text{ V}, I_D = 13 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_D = 13 \text{ A}, T_J = 125 ^{\circ}\text{C}$ $V_{GS} = 10 \text{ V}, I_D = 14 \text{ A}$		8.2 11.5 6.8	9.5 16 8	mΩ
I _{D(on)}	On-State Drain Current	$V_{GS} = 10 \text{ V}, I_D = 14 \text{ A}$ $V_{GS} = 10 \text{ V}, V_{DS} = 5 \text{ V}$	50			Α
g _{FS}	Forward Transconductance	$V_{DS} = 10 \text{ V}, \qquad I_{D} = 15 \text{ A}$		75		S
Dynamic	Characteristics		•			•
C _{iss}	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$		5070		pF
Coss	Output Capacitance	f = 1.0 MHz		550		pF
C _{rss}	Reverse Transfer Capacitance	7		230		pF
Switchir	ng Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 10 \text{ V}, I_{D} = 1 \text{ A},$		17	25	ns
t _r	Turn-On Rise Time	$V_{GS} = 4.5 \text{ V}, R_{GEN} = 6 \Omega$		18	25	ns
t _{d(off)}	Turn-Off Delay Time	1		69	100	ns
t _f	Turn-Off Fall Time			29	42	ns
Q_g	Total Gate Charge	$V_{DS} = 15 \text{ V}, I_{D} = 15 \text{ A},$		33	46	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = 4.5 \text{ V}$		7.5		nC
Q _{gd}	Gate-Drain Charge	1		6.8		nC
Drain-S	ource Diode Characteristics	and Maximum Ratings				
Is	Maximum Continuous Drain-Source				2.7	Α
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = 2.7 \text{ A}$ (Note 2)		0.7	1.2	V

Notes:

^{1.} $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the drain tab. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.





b) $R_{\theta JA} = 96^{\circ} \text{C/W}$ on a minimum mounting pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < $300\,\mu\text{s},$ Duty Cycle < 2.0%

Typical Characteristics

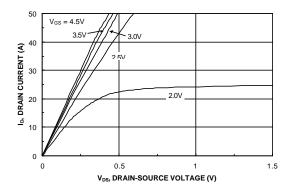


Figure 1. On-Region Characteristics.

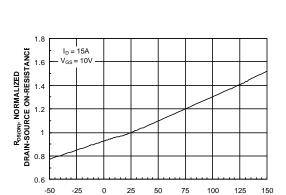


Figure 3. On-Resistance Variation with Temperature.

T_J, JUNCTION TEMPERATURE (°C)

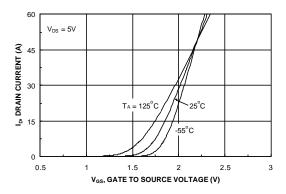


Figure 5. Transfer Characteristics.

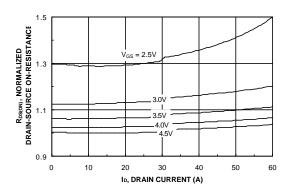


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

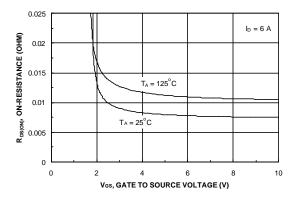


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

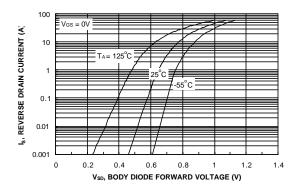
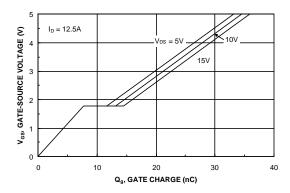


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



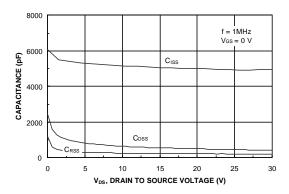
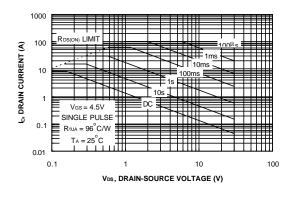


Figure 7. Gate Charge Characteristics.





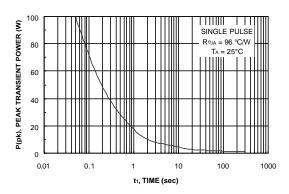


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

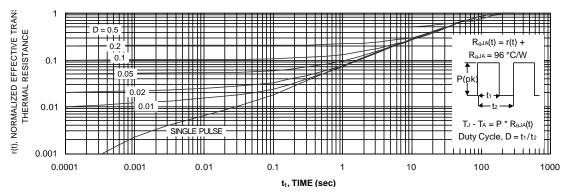


Figure 11. Transient Thermal Response Curve.

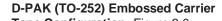
Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

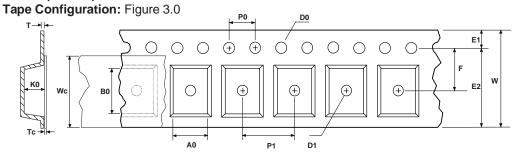
TO-252 Tape and Reel Data and Package Dimensions FAIRCHILD SEMICONDUCTOR TM D-PAK (TO-252) Packaging Configuration: Figure 1.0 Packaging Description: To-252 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2500 units per 13' or 330cm diameter reel. The reels are dark blue in color and is made of polystyrene plastic (anti-static coated). This and some other options are further described in the Packaging Information table. Antistatic Cover Tape ESD Label These full reels are individually barcode labeled and placed inside a standard intermediate box (illustrated in figure 1.0) made of recyclable corrugated brown paper. One box contains two reels maximum. And these boxes are placed inside a barcode labeled shipping box which comes in different sizes depending on the number of parts shipped. Static Dissipative **Embossed Carrier Tape** F63TNR Label D-PAK (TO-252) Packaging Information Packaging Option D-PAK (TO-252) Unit Orientation Packaging type TNR Qty per Reel/Tube/Bag 2.500 Reel Size 13" Dia Box Dimension (mm) 359x359x57 5,000 Max qty per Box 359mm x 359mm x 57mm Weight per unit (gm) 0.300 Standard Intermediate box Weight per Reel(kg) 1.200 **ESD Label** F63TNR Label sample F63TNR Label D/C1: Z9942 D/C2: SPEC REV: CPN: QTY1: QTY2: TO-252 (D-PAK) Tape Leader and **Trailer Configuration:** Figure 2.0 \bigcirc \bigcirc \bigcirc \bigcirc \bigcirc 0 0 0 0 Components Trailer Tape 640mm minimum or 1680mm minimum or

80 empty pockets

210 empty pockets







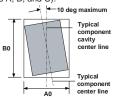
User Direction of Feed

	Dimensions are in millimeter													
Pkg type	A0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
TO252 (24mm)	6.90 +/-0.10	10.50 +/-0.10	16.0 +/-0.3	1.55 +/-0.05	1.5 +/-0.10	1.75 +/-0.10	14.25 min	7.50 +/-0.10	8.0 +/-0.1	4.0 +/-0.1	2.65 +/-0.10	0.30 +/-0.05	13.0 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



Sketch B (Top View)

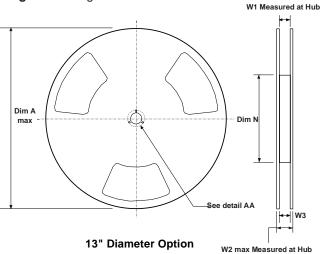
Component Rotation

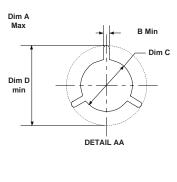


Sketch C (Top View)

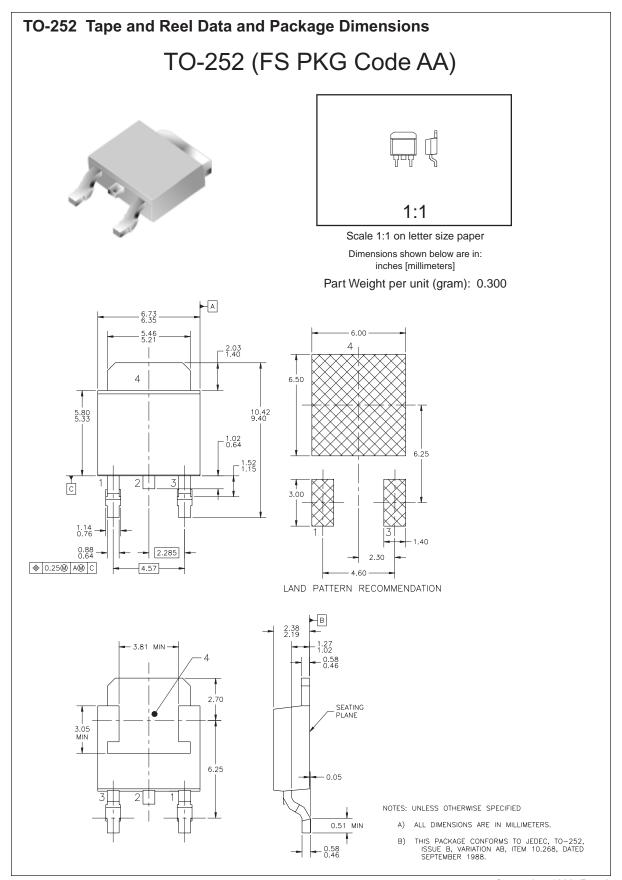
Component lateral movement

D-PAK (TO-252) Reel Configuration: Figure 4.0





Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
164mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.646 +0.078/-0.000 16.4 +2/0	0.882 22.4	0.626 - 0.764 15.9 - 19.4



TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

FACT™ QFET™ FACT Quiet Series™ QS™

FAST[®] Quiet Series[™] SuperSOT[™]-3 GTO[™] SuperSOT[™]-6

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

- 1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.